

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

APT43F60L

FEATURES

- Drain Current –I_D= 45A@ T_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage-: V_{DSS}=600V(Min)
- Static Drain-Source On-Resistance : R_{DS(on)} =0.15 Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

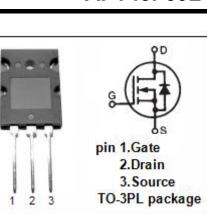
• Designed for use in switch mode power supplies and general purpose applications.

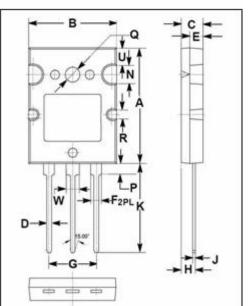
| SYMBOL | PARAMETER | VALUE | UNIT | | |
|------------------|-------------------------------------|---------|------|--|--|
| V _{DSS} | Drain-Source Voltage | 600 | V | | |
| V _{GS} | Gate-Source Voltage-Continuous | ±30 | V | | |
| ID | Drain Current-Continuous | 45 | А | | |
| I _{DM} | Drain Current-Single Pluse | 160 | А | | |
| PD | Total Dissipation @Tc=25℃ | 780 | W | | |
| TJ | Max. Operating Junction Temperature | -55~150 | °C | | |
| T _{stg} | Storage Temperature | -55~150 | °C | | |

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|--------------------------------------|------|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 0.16 | °C/W |





| | m | m |
|-----|-------|-------|
| DIM | MIN | MAX |
| A | 25.50 | 26.50 |
| В | 19.80 | 20.20 |
| С | 4.50 | 5.50 |
| D | 0.90 | 1.10 |
| E | 2.80 | 3.20 |
| F | 2.40 | 2.60 |
| G | 10.80 | 11.00 |
| Н | 3.10 | 3.30 |
| J | 0.50 | 0.70 |
| Κ | 20.00 | 21.00 |
| N | 3.90 | 4.50 |
| P | 2.40 | 2.60 |
| Q | 3.10 | 3.50 |
| R | 1.90 | 2.60 |
| U | 3.90 | 4.10 |
| W | 2.90 | 3.25 |

isc website: <u>www.iscsemi.com</u>



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ELECTRICAL CHARACTERISTICS

TJ=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | МАХ | UNIT |
|----------------------|---------------------------------|--|-----|-------------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 0.25mA | 600 | | V |
| V _{GS(th)} | Gate Threshold Voltage | V_{DS} = V_{GS} ; I_D = 2.5mA | 2.5 | 5 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =21A | | 0.15 | Ω |
| lgss | Gate-Body Leakage Current | V _{GS} = ±30V;V _{DS} = 0 | | ±100 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V_{DS} = 600V; V_{GS} = 0 V_{DS} = 600V; V_{GS} = 0@T _J =125°C | | 250 1000 | μA |
| V _{SD} | Forward On-Voltage | I _S =-21A; V _{GS} = 0 | | 1.0 | V |

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